



## 2SD389

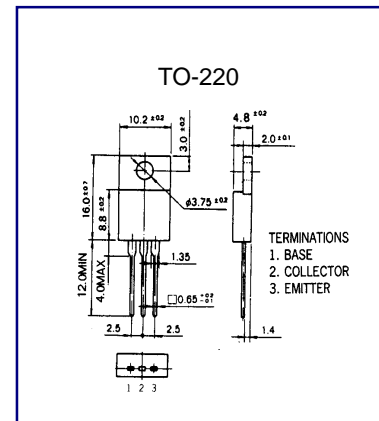
## NPN EPITAXIAL SILICON TRANSISTOR

### LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SB507

### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	60	V
Collector-Emitter Voltage	V <sub>CE0</sub>	60	V
Emitter-Base voltage	V <sub>EB0</sub>	7	V
Collector Current (DC)	I <sub>C</sub>	4	A
Collector Dissipation ( $T_c=25^\circ\text{C}$ )	P <sub>C</sub>	30	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V , I <sub>E</sub> =0			100	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 7V , I <sub>C</sub> =0			100	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = 3V , I <sub>C</sub> =1A		70		
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2A , I <sub>B</sub> =0.2A			1.0	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> =0.5A		18		MHZ